

1Mb x 36, 2Mb x 18 36Mb SYNCHRONOUS PIPELINED, SINGLE CYCLE DESELECT STATIC RAM

MARCH 2008

FEATURES

- Internal self-timed write cycle
- Individual Byte Write Control and Global Write
- Clock controlled, registered address, data and control
- Burst sequence control using MODE input
- Three chip enable option for simple depth expansion and address pipelining
- Common data inputs and data outputs
- Auto Power-down during deselect
- Single cycle deselect
- Snooze MODE for reduced-power standby
- Power Supply
LPS: $V_{DD} 3.3V \pm 5\%$, $V_{DDQ} 3.3V/2.5V \pm 5\%$
VPS: $V_{DD} 2.5V \pm 5\%$, $V_{DDQ} 2.5V \pm 5\%$
- JEDEC 100-Pin TQFP and 165-ball PBGA packages
- Lead-free available

DESCRIPTION

The *ISSI* IS61LPS/VPS102436A and IS61LPS/VPS204818A are high-speed, low-power synchronous static RAMs designed to provide burstable, high-performance memory for communication and networking applications. The IS61LPS/VPS102436A is organized as 1,048,476 words by 36 bits. The IS61LPS/VPS204818A is organized as 2M-word by 18 bits. Fabricated with *ISSI*'s advanced CMOS technology, the device integrates a 2-bit burst counter, high-speed SRAM core, and high-drive capability outputs into a single monolithic circuit. All synchronous inputs pass through registers controlled by a positive-edge-triggered single clock input.

Write cycles are internally self-timed and are initiated by the rising edge of the clock input. Write cycles can be one to four bytes wide as controlled by the write control inputs.

Separate byte enables allow individual bytes to be written. The byte write operation is performed by using the byte write enable (\overline{BWE}) input combined with one or more individual byte write signals (\overline{BWx}). In addition, Global Write (\overline{GW}) is available for writing all bytes at one time, regardless of the byte write controls.

Bursts can be initiated with either \overline{ADSP} (Address Status Processor) or \overline{ADSC} (Address Status Cache Controller) input pins. Subsequent burst addresses can be generated internally and controlled by the \overline{ADV} (burst address advance) input pin.

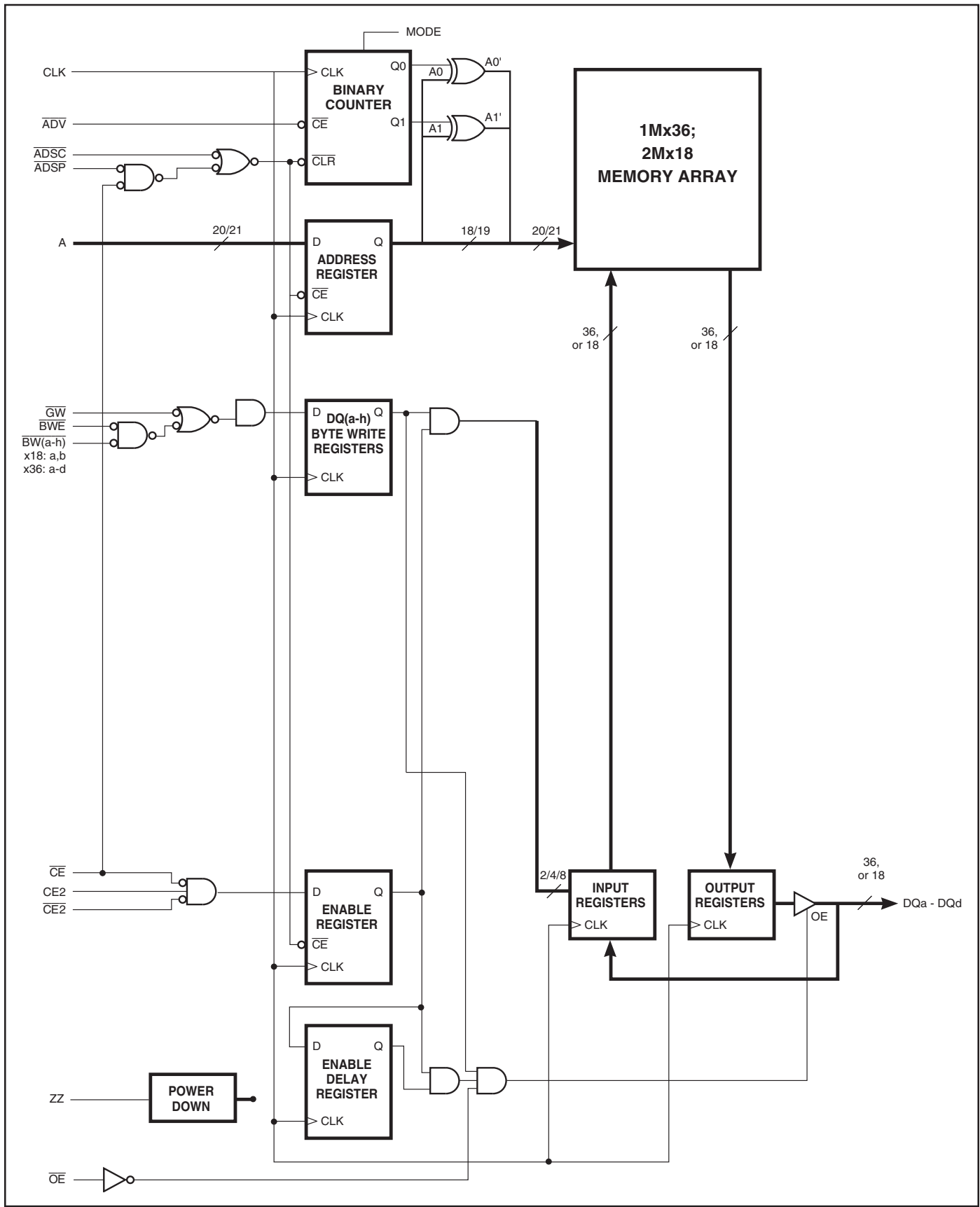
The mode pin is used to select the burst sequence order, Linear burst is achieved when this pin is tied LOW. Interleave burst is achieved when this pin is tied HIGH or left floating.

FAST ACCESS TIME

Symbol	Parameter	200	166	Units
t_{kQ}	Clock Access Time	3.1	3.5	ns
t_{kC}	Cycle Time	5	6	ns
	Frequency	200	166	MHz

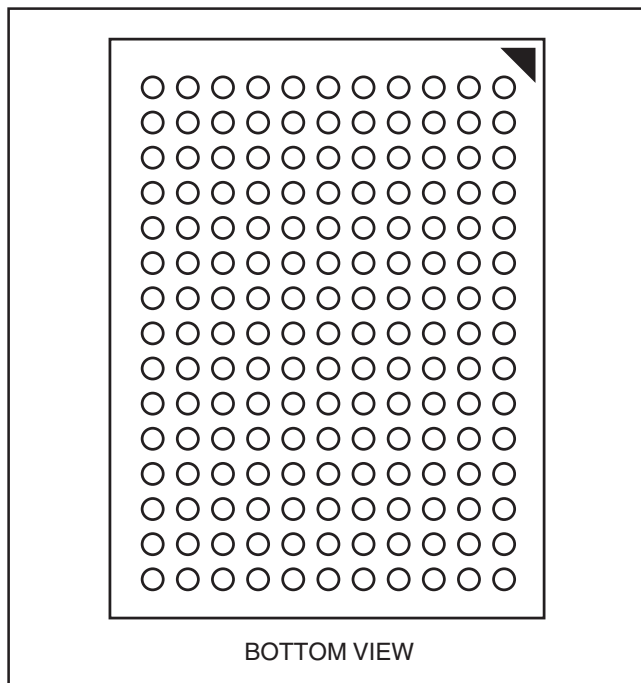
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BLOCK DIAGRAM



165-PIN BGA

165-Ball, 13x15 mm BGA
1mm Ball Pitch, 11x15 Ball Array



165 PBGA PACKAGE PIN CONFIGURATION

1M x 36 (TOP VIEW)

	1	2	3	4	5	6	7	8	9	10	11
A	NC	A	\overline{CE}	\overline{BWc}	\overline{BWb}	$\overline{CE2}$	\overline{BWE}	\overline{ADSC}	\overline{ADV}	A	NC
B	NC	A	CE2	\overline{BWd}	\overline{BWa}	CLK	\overline{GW}	\overline{OE}	\overline{ADSP}	A	NC
C	DQPc	NC	VDDQ	Vss	Vss	Vss	Vss	Vss	VDDQ	NC	DQPb
D	DQc	DQc	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQb	DQb
E	DQc	DQc	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQb	DQb
F	DQc	DQc	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQb	DQb
G	DQc	DQc	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQb	DQb
H	NC	NC	NC	VDD	Vss	Vss	Vss	VDD	NC	NC	ZZ
J	DQd	DQd	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQa	DQa
K	DQd	DQd	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQa	DQa
L	DQd	DQd	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQa	DQa
M	DQd	DQd	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQa	DQa
N	DQPd	NC	VDDQ	Vss	NC	A	NC	Vss	VDDQ	NC	DQPd
P	NC	NC	A	A	NC	A1*	NC	A	A	A	A
R	MODE	A	A	A	NC	A0*	NC	A	A	A	A

Note: * A0 and A1 are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

Symbol	Pin Name
A	Address Inputs
A0, A1	Synchronous Burst Address Inputs
\overline{ADV}	Synchronous Burst Address Advance
\overline{ADSP}	Address Status Processor
\overline{ADSC}	Address Status Controller
\overline{GW}	Global Write Enable
CLK	Synchronous Clock
\overline{CE} , $\overline{CE2}$, CE2	Synchronous Chip Select
\overline{BWx} (x=a,b,c,d)	Synchronous Byte Write Controls

Symbol	Pin Name
\overline{BWE}	Byte Write Enable
\overline{OE}	Output Enable
ZZ	Power Sleep Mode
MODE	Burst Sequence Selection
NC	No Connect
DQx	Data Inputs/Outputs
DQPx	Data Inputs/Outputs
VDD	3.3V/2.5V Power Supply
VDDQ	Isolated Output Power Supply 3.3V/2.5V
Vss	Ground

165 PBGA PACKAGE PIN CONFIGURATION

2M x 18 (TOP VIEW)

	1	2	3	4	5	6	7	8	9	10	11
A	NC	A	\overline{CE}	\overline{BWb}	NC	$\overline{CE2}$	\overline{BWE}	\overline{ADSC}	\overline{ADV}	A	A
B	NC	A	CE2	NC	\overline{BWa}	CLK	\overline{GW}	\overline{OE}	\overline{ADSP}	A	NC
C	NC	NC	V _{DDQ}	V _{SS}	V _{SS}	V _{SS}	V _{SS}	V _{SS}	V _{DDQ}	NC	DQP _a
D	NC	DQ _b	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	NC	DQ _a
E	NC	DQ _b	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	NC	DQ _a
F	NC	DQ _b	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	NC	DQ _a
G	NC	DQ _b	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	NC	DQ _a
H	NC	NC	NC	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	NC	NC	ZZ
J	DQ _b	NC	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	DQ _a	NC
K	DQ _b	NC	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	DQ _a	NC
L	DQ _b	NC	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	DQ _a	NC
M	DQ _b	NC	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	DQ _a	NC
N	DQP _b	NC	V _{DDQ}	V _{SS}	NC	A	NC	V _{SS}	V _{DDQ}	NC	NC
P	NC	NC	A	A	NC	A ₁ *	NC	A	A	A	A
R	MODE	A	A	A	NC	A ₀ *	NC	A	A	A	A

Note: * A₀ and A₁ are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

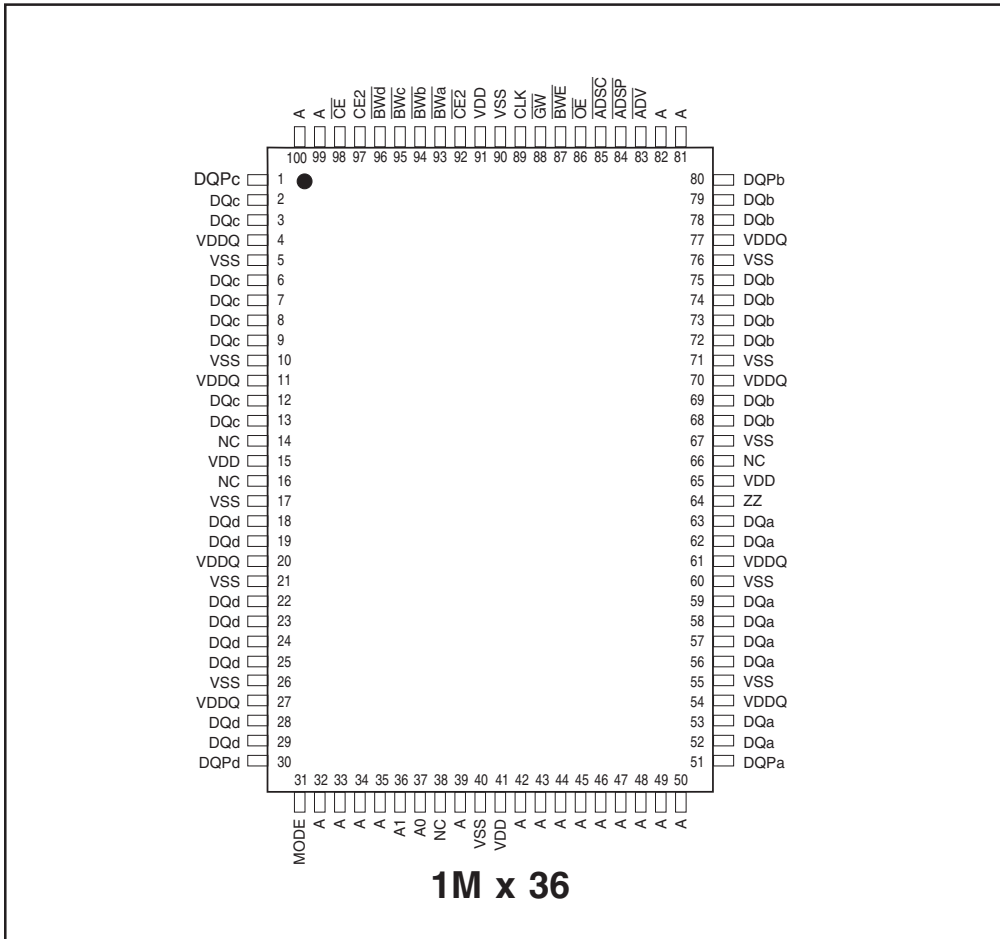
PIN DESCRIPTIONS

Symbol	Pin Name
A	Address Inputs
A ₀ , A ₁	Synchronous Burst Address Inputs
\overline{ADV}	Synchronous Burst Address Advance
\overline{ADSP}	Address Status Processor
\overline{ADSC}	Address Status Controller
\overline{GW}	Global Write Enable
CLK	Synchronous Clock
\overline{CE} , $\overline{CE2}$, CE2	Synchronous Chip Select
\overline{BWx} (x=a,b)	Synchronous Byte Write Controls

Symbol	Pin Name
\overline{BWE}	Byte Write Enable
\overline{OE}	Output Enable
ZZ	Power Sleep Mode
MODE	Burst Sequence Selection
NC	No Connect
DQ _x	Data Inputs/Outputs
DQP _x	Data Inputs/Outputs
V _{DD}	3.3V/2.5V Power Supply
V _{DDQ}	Isolated Output Power Supply 3.3V/2.5V
V _{SS}	Ground

PIN CONFIGURATION

100-PIN TQFP



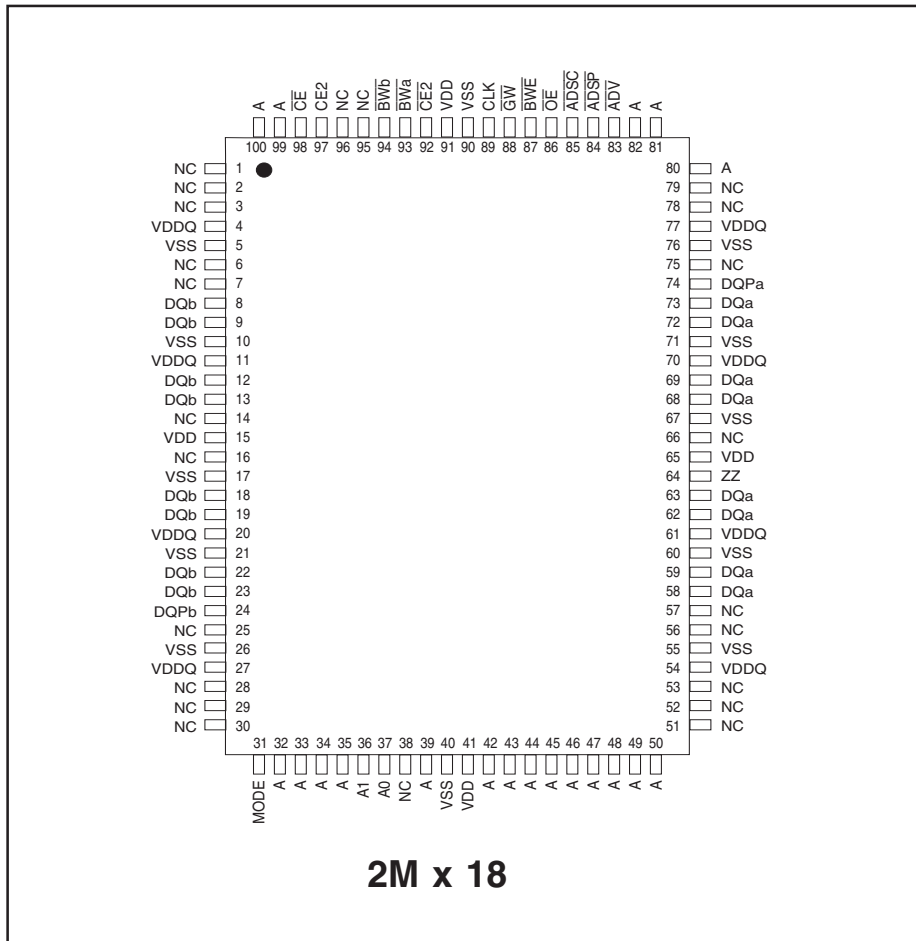
PIN DESCRIPTIONS

A0, A1	Synchronous Address Inputs. These pins must tied to the two LSBs of the address bus.
A	Synchronous Address Inputs
$\overline{\text{ADSC}}$	Synchronous Controller Address Status
$\overline{\text{ADSP}}$	Synchronous Processor Address Status
$\overline{\text{ADV}}$	Synchronous Burst Address Advance
$\overline{\text{BWA-BWd}}$	Synchronous Byte Write Enable
$\overline{\text{BWE}}$	Synchronous Byte Write Enable
$\overline{\text{CE}}, \overline{\text{CE2}}, \text{CE2}$	Synchronous Chip Enable
CLK	Synchronous Clock

DQa-DQd	Synchronous Data Input/Output
DQPa-DQPd	Parity Data Input/Output
$\overline{\text{GW}}$	Synchronous Global Write Enable
MODE	Burst Sequence Mode Selection
$\overline{\text{OE}}$	Output Enable
VDD	3.3V/2.5V Power Supply
VDDQ	Isolated Output Buffer Supply: 3.3V/2.5V
VSS	Ground
ZZ	Snooze Enable

PIN CONFIGURATION

100-PIN TQFP



PIN DESCRIPTIONS

A0, A1	Synchronous Address Inputs. These pins must be tied to the two LSBs of the address bus.	DQPa-DQPa	Parity Data I/O; DQPa is parity for DQa1-8; DQPa is parity for DQb1-8
A	Synchronous Address Inputs	\overline{GW}	Synchronous Global Write Enable
\overline{ADSC}	Synchronous Controller Address Status	MODE	Burst Sequence Mode Selection
\overline{ADSP}	Synchronous Processor Address Status	\overline{OE}	Output Enable
\overline{ADV}	Synchronous Burst Address Advance	VDD	3.3V/2.5V Power Supply
\overline{BWA} - \overline{BWb}	Synchronous Byte Write Enable	VDDQ	Isolated Output Buffer Supply: 3.3V/2.5V
\overline{BWE}	Synchronous Byte Write Enable	VSS	Ground
\overline{CE} , $\overline{CE2}$, $\overline{CE2}$	Synchronous Chip Enable	\overline{ZZ}	Snooze Enable
CLK	Synchronous Clock		
DQa-DQb	Synchronous Data Input/Output		

TRUTH TABLE⁽¹⁻⁸⁾ (3CE option)

OPERATION	ADDRESS	\overline{CE}	$\overline{CE2}$	CE2	ZZ	\overline{ADSP}	\overline{ADSC}	\overline{ADV}	\overline{WRITE}	\overline{OE}	CLK	DQ
Deselect Cycle, Power-Down	None	H	X	X	L	X	L	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	X	L	L	L	X	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	H	X	L	L	X	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	X	L	L	H	L	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	H	X	L	H	L	X	X	X	L-H	High-Z
Snooze Mode, Power-Down	None	X	X	X	H	X	X	X	X	X	X	High-Z
Read Cycle, Begin Burst	External	L	L	H	L	L	X	X	X	L	L-H	Q
Read Cycle, Begin Burst	External	L	L	H	L	L	X	X	X	H	L-H	High-Z
Write Cycle, Begin Burst	External	L	L	H	L	H	L	X	L	X	L-H	D
Read Cycle, Begin Burst	External	L	L	H	L	H	L	X	H	L	L-H	Q
Read Cycle, Begin Burst	External	L	L	H	L	H	L	X	H	H	L-H	High-Z
Read Cycle, Continue Burst	Next	X	X	X	L	H	H	L	H	L	L-H	Q
Read Cycle, Continue Burst	Next	X	X	X	L	H	H	L	H	H	L-H	High-Z
Read Cycle, Continue Burst	Next	H	X	X	L	X	H	L	H	L	L-H	Q
Read Cycle, Continue Burst	Next	H	X	X	L	X	H	L	H	H	L-H	High-Z
Write Cycle, Continue Burst	Next	X	X	X	L	H	H	L	L	X	L-H	D
Write Cycle, Continue Burst	Next	H	X	X	L	X	H	L	L	X	L-H	D
Read Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	H	L	L-H	Q
Read Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	H	H	L-H	High-Z
Read Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	H	L	L-H	Q
Read Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	H	H	L-H	High-Z
Write Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	L	X	L-H	D
Write Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	L	X	L-H	D

NOTE:

1. X means "Don't Care." H means logic HIGH. L means logic LOW.
2. For \overline{WRITE} , L means one or more byte write enable signals ($\overline{BWA-h}$) and \overline{BWE} are LOW or \overline{GW} is LOW. $\overline{WRITE} = H$ for all \overline{BWx} , \overline{BWE} , \overline{GW} HIGH.
3. \overline{BWA} enables WRITES to DQa's and DQPc. \overline{BWB} enables WRITES to DQb's and DQpb. \overline{BWC} enables WRITES to DQc's and DQpc. \overline{BWD} enables WRITES to DQd's and DQpd. DQPa-DQPd are available on the x36 version.
4. All inputs except \overline{OE} and ZZ must meet setup and hold times around the rising edge (LOW to HIGH) of CLK.
5. Wait states are inserted by suspending burst.
6. For a WRITE operation following a READ operation, \overline{OE} must be HIGH before the input data setup time and held HIGH during the input data hold time.
7. This device contains circuitry that will ensure the outputs will be in High-Z during power-up.
8. \overline{ADSP} LOW always initiates an internal READ at the L-H edge of CLK. A WRITE is performed by setting one or more byte write enable signals and \overline{BWE} LOW or \overline{GW} LOW for the subsequent L-H edge of CLK. See WRITE timing diagram for clarification.

TRUTH TABLE⁽¹⁻⁸⁾ (1CE option)

NEXT CYCLE	ADDRESS	\overline{CE}	\overline{ADSP}	\overline{ADSC}	\overline{ADV}	\overline{WRITE}	\overline{OE}	DQ
Deselected	None	H	X	L	X	X	X	High-Z
Read, Begin Burst	External	L	L	X	X	X	L	Q
Read, Begin Burst	External	L	L	X	X	X	H	High-Z
Write, Begin Burst	External	L	H	L	X	L	X	D
Read, Begin Burst	External	L	H	L	X	H	L	Q
Read, Begin Burst	External	L	H	L	X	H	H	High-Z
Read, Continue Burst	Next	X	H	H	L	H	L	Q
Read, Continue Burst	Next	X	H	H	L	H	H	High-Z
Read, Continue Burst	Next	H	X	H	L	H	L	Q
Read, Continue Burst	Next	H	X	H	L	H	H	High-Z
Write, Continue Burst	Next	X	H	H	L	L	X	D
Write, Continue Burst	Next	H	X	H	L	L	X	D
Read, Suspend Burst	Current	X	H	H	H	H	L	Q
Read, Suspend Burst	Current	X	H	H	H	H	H	High-Z
Read, Suspend Burst	Current	H	X	H	H	H	L	Q
Read, Suspend Burst	Current	H	X	H	H	H	H	High-Z
Write, Suspend Burst	Current	X	H	H	H	L	X	D
Write, Suspend Burst	Current	H	X	H	H	L	X	D

NOTE:

1. X means "Don't Care." H means logic HIGH. L means logic LOW.
2. For \overline{WRITE} , L means one or more byte write enable signals ($\overline{BWA-h}$) and \overline{BWE} are LOW or \overline{GW} is LOW. $\overline{WRITE} = H$ for all \overline{BWx} , \overline{BWE} , \overline{GW} HIGH.
3. \overline{BWA} enables WRITES to DQa's and DQPd. \overline{BWb} enables WRITES to DQb's and DQPb. \overline{BWC} enables WRITES to DQc's and DQPc. \overline{BWD} enables WRITES to DQd's and DQPd. DQPa-DQPd are available on the x36 version.
4. All inputs except \overline{OE} and ZZ must meet setup and hold times around the rising edge (LOW to HIGH) of CLK.
5. Wait states are inserted by suspending burst.
6. For a WRITE operation following a READ operation, \overline{OE} must be HIGH before the input data setup time and held HIGH during the input data hold time.
7. This device contains circuitry that will ensure the outputs will be in High-Z during power-up.
8. \overline{ADSP} LOW always initiates an internal READ at the L-H edge of CLK. A WRITE is performed by setting one or more byte write enable signals and \overline{BWE} LOW or \overline{GW} LOW for the subsequent L-H edge of CLK. See WRITE timing diagram for clarification.

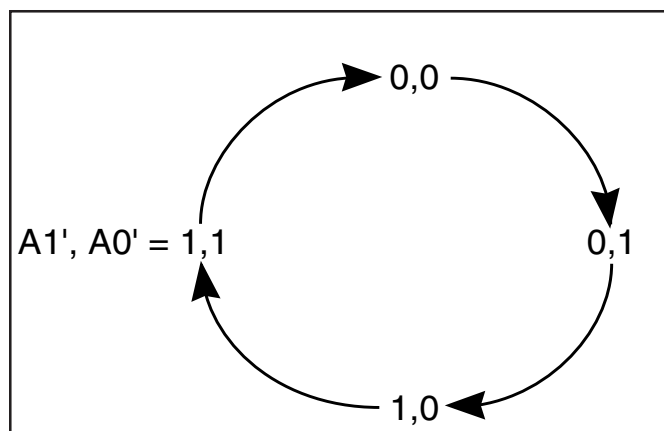
PARTIAL TRUTH TABLE

Function	\overline{GW}	\overline{BWE}	\overline{BWA}	\overline{BWb}	\overline{BWC}	\overline{BWD}
Read	H	H	X	X	X	X
Read	H	L	H	H	H	H
Write Byte 1	H	L	L	H	H	H
Write All Bytes	H	L	L	L	L	L
Write All Bytes	L	X	X	X	X	X

INTERLEAVED BURST ADDRESS TABLE (MODE = V_{DD} or No Connect)

External Address A1 A0	1st Burst Address A1 A0	2nd Burst Address A1 A0	3rd Burst Address A1 A0
00	01	10	11
01	00	11	10
10	11	00	01
11	10	01	00

LINEAR BURST ADDRESS TABLE (MODE = V_{SS})



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	-55 to +150	°C
P _D	Power Dissipation	1.6	W
I _{OUT}	Output Current (per I/O)	100	mA
V _{IN} , V _{OUT}	Voltage Relative to V _{SS} for I/O Pins	-0.5 to V _{DDQ} + 0.5	V
V _{IN}	Voltage Relative to V _{SS} for Address and Control Inputs	-0.5 to V _{DD} + 0.5	V
V _{DD}	Voltage on V _{DD} Supply Relative to V _{SS}	-0.5 to 4.6	V

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, precautions may be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.
3. This device contains circuitry that will ensure the output devices are in High-Z at power up.

OPERATING RANGE (IS61LPSXXXX)

Range	Ambient Temperature	V _{DD}	V _{DDQ}
Commercial	0°C to +70°C	3.3V ± 5%	3.3V / 2.5V ± 5%
Industrial	-40°C to +85°C	3.3V ± 5%	3.3V / 2.5V ± 5%

OPERATING RANGE (IS61VPSXXXX)

Range	Ambient Temperature	V _{DD}	V _{DDQ}
Commercial	0°C to +70°C	2.5V ± 5%	2.5V ± 5%
Industrial	-40°C to +85°C	2.5V ± 5%	2.5V ± 5%

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	3.3V		2.5V		Unit
			Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = -4.0 mA (3.3V) I _{OH} = -1.0 mA (2.5V)	2.4	—	2.0	—	V
V _{OL}	Output LOW Voltage	I _{OL} = 8.0 mA (3.3V) I _{OL} = 1.0 mA (2.5V)	—	0.4	—	0.4	V
V _{IH}	Input HIGH Voltage		2.0	V _{DD} + 0.3	1.7	V _{DD} + 0.3	V
V _{IL}	Input LOW Voltage		-0.3	0.8	-0.3	0.7	V
I _{LI}	Input Leakage Current	V _{SS} ≤ V _{IN} ≤ V _{DD} ⁽¹⁾	-5	5	-5	5	μA
I _{LO}	Output Leakage Current	V _{SS} ≤ V _{OUT} ≤ V _{DDQ} , OE = V _{IH}	-5	5	-5	5	μA

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions	Temp. range	-200 MAX		-166 MAX		Unit
				x18	x36	x18	x36	
I _{CC}	AC Operating Supply Current	Device Selected, OE = V _{IH} , ZZ ≤ V _{IL} , All Inputs ≤ 0.2V or ≥ V _{DD} - 0.2V, Cycle Time ≥ t _{CC} min.	Com. Ind. typ. ⁽²⁾	450 475 390	450 475	400 450 340	400 450	mA
I _{SB}	Standby Current TTL Input	Device Deselected, V _{DD} = Max., All Inputs ≤ V _{IL} or ≥ V _{IH} , ZZ ≤ V _{IL} , f = Max.	Com. Ind.	150 150	150 150	120 120	120 120	mA
I _{SBI}	Standby Current CMOS Input	Device Deselected, V _{DD} = Max., V _{IN} ≤ V _{SS} + 0.2V or ≥ V _{DD} - 0.2V f = 0	Com. Ind. typ. ⁽²⁾	110 140 75	110 140	110 140 75	110 140	mA

Note:

- MODE pin has an internal pullup and should be tied to V_{DD} or V_{SS}. It exhibits ±100μA maximum leakage current when tied to ≤ V_{SS} + 0.2V or ≥ V_{DD} - 0.2V.
- Typical values are measured at V_{CC} = 3.3V, T_A = 25°C and not 100% tested.

CAPACITANCE^(1,2)

Symbol	Parameter	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	6	pF
C _{OUT}	Input/Output Capacitance	V _{OUT} = 0V	8	pF

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, V_{DD} = 3.3V.

3.3V I/O AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	1.5 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1 and 2

AC TEST LOADS

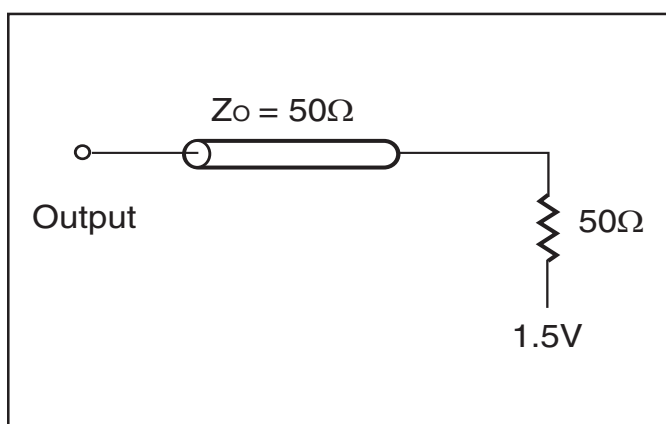


Figure 1

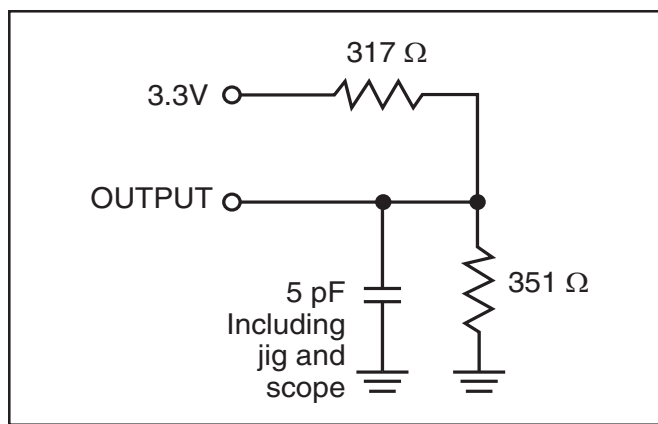


Figure 2

2.5V I/O AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 2.5V
Input Rise and Fall Times	1.5 ns
Input and Output Timing and Reference Level	1.25V
Output Load	See Figures 3 and 4

2.5 I/O OUTPUT LOAD EQUIVALENT

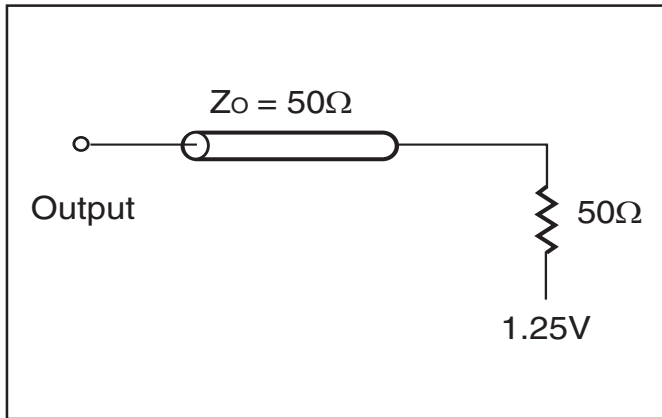


Figure 3

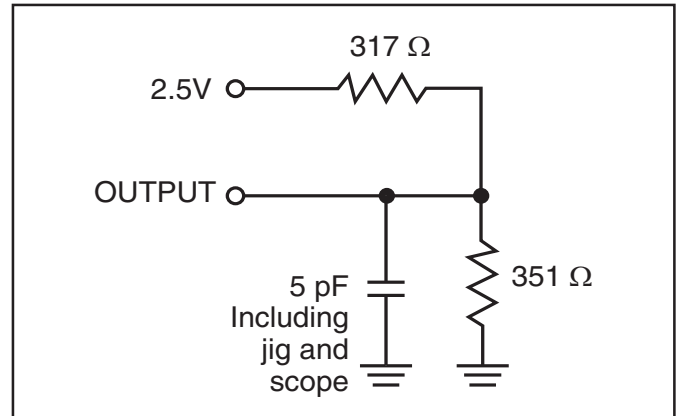


Figure 4

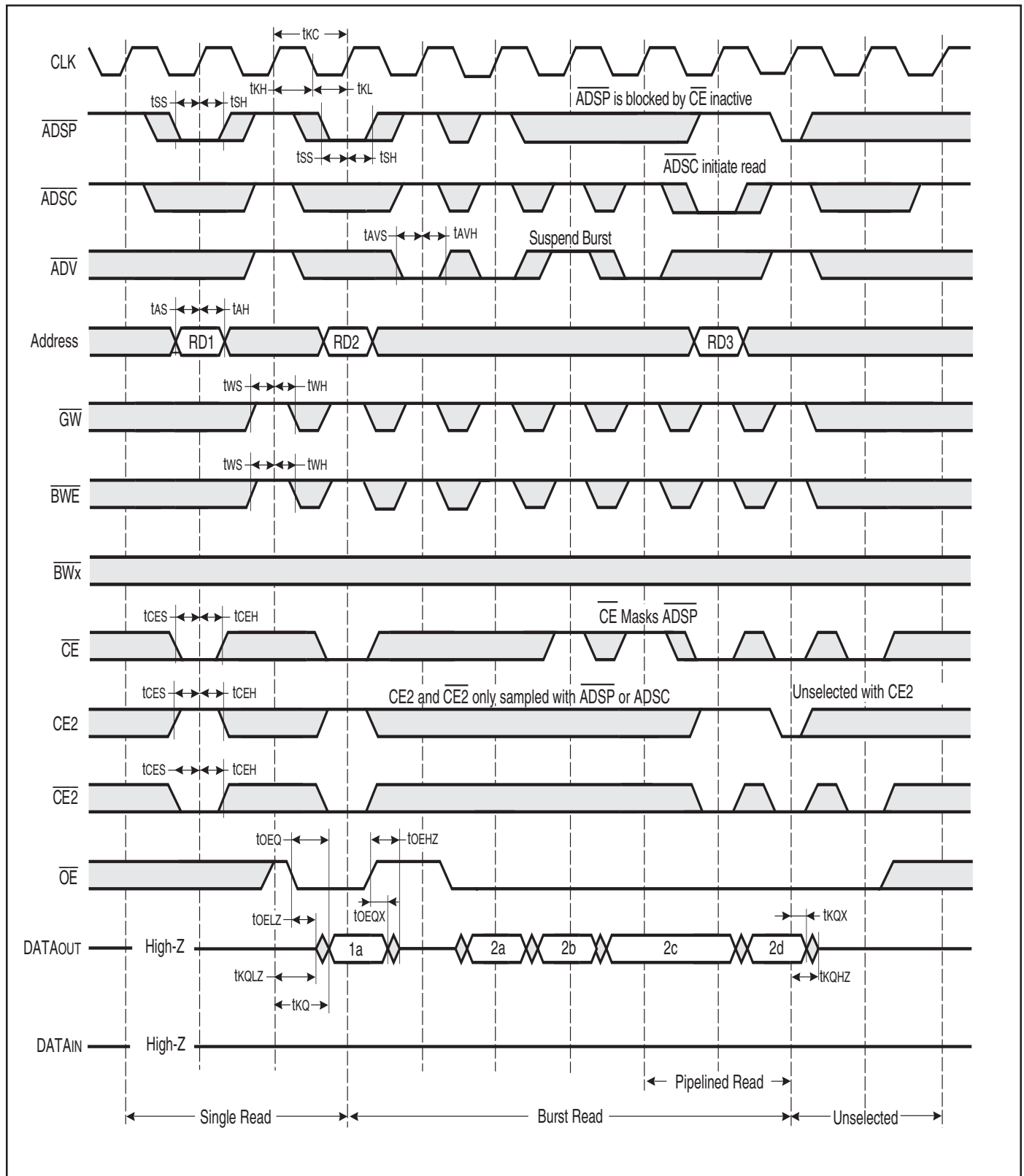
READ/WRITE CYCLE SWITCHING CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	-200		-166		Unit
		Min.	Max.	Min.	Max.	
f _{MAX}	Clock Frequency	—	200	—	166	MHz
t _{KC}	Cycle Time	5	—	6	—	ns
t _{KH}	Clock High Time	2	—	2.4	—	ns
t _{KL}	Clock Low Time	2	—	2.4	—	ns
t _{KQ}	Clock Access Time	—	3.1	—	3.5	ns
t _{KQX} ⁽²⁾	Clock High to Output Invalid	1.5	—	1.5	—	ns
t _{KQLZ} ^(2,3)	Clock High to Output Low-Z	1	—	1	—	ns
t _{KQHZ} ^(2,3)	Clock High to Output High-Z	—	3.0	—	3.4	ns
t _{OEQ}	Output Enable to Output Valid	—	3.1	—	3.5	ns
t _{OEQX} ⁽²⁾	Output Disable to Output Invalid	0	—	0	—	ns
t _{OELZ} ^(2,3)	Output Enable to Output Low-Z	0	—	0	—	ns
t _{OEHZ} ^(2,3)	Output Disable to Output High-Z	—	3.0	—	3.4	ns
t _{AS}	Address Setup Time	1.4	—	1.5	—	ns
t _{SS}	Address Status Setup Time	1.4	—	1.5	—	ns
t _{WS}	Read/Write Setup Time	1.4	—	1.5	—	ns
t _{CES}	Chip Enable Setup Time	1.4	—	1.5	—	ns
t _{AVS}	Address Advance Setup Time	1.4	—	1.5	—	ns
t _{DS}	Data Setup Time	1.4	—	1.5	—	ns
t _{AH}	Address Hold Time	0.4	—	0.5	—	ns
t _{SH}	Address Status Hold Time	0.4	—	0.3	—	ns
t _{WH}	Write Hold Time	0.4	—	0.5	—	ns
t _{CEH}	Chip Enable Hold Time	0.4	—	0.5	—	ns
t _{AVH}	Address Advance Hold Time	0.4	—	0.5	—	ns
t _{DH}	Data Hold Time	0.4	—	0.5	—	ns
t _{PDS}	ZZ High to Power Down	—	2	—	2	cyc
t _{PUS}	ZZ Low to Power Down	—	2	—	2	cyc

Note:

1. Configuration signal MODE is static and must not change during normal operation.
2. Guaranteed but not 100% tested. This parameter is periodically sampled.
3. Tested with load in Figure 2.

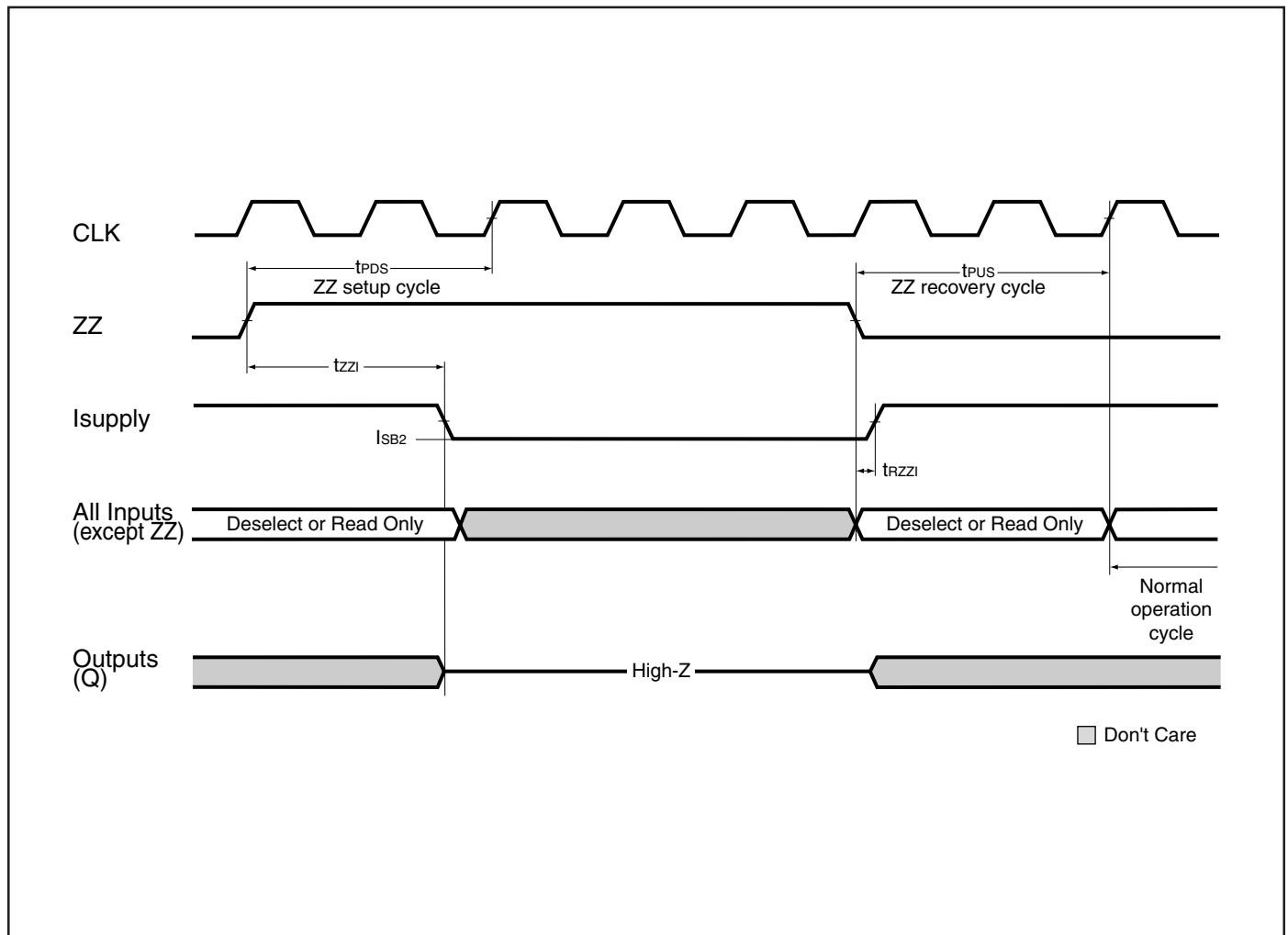
READ/WRITE CYCLE TIMING



SNOOZE MODE ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Temperature	Conditions	Min.	Max.	Unit
ISB2	Current during SNOOZE MODE	Com. Ind.	ZZ ≥ Vih	—	60 90	mA
tPDS	ZZ active to input ignored			—	2	cycle
tPUS	ZZ inactive to input sampled			2	—	cycle
tZZI	ZZ active to SNOOZE current			—	2	cycle
tRZZI	ZZ inactive to exit SNOOZE current			0	—	ns

SNOOZE MODE TIMING



ORDERING INFORMATION (3.3V core/2.5V-3.3V I/O)**Commercial Range: 0°C to +70°C**

Configuration	Frequency	Order Part Number	Package
1Mx36			
	166	IS61LPS102436A-166TQ	100 TQFP
		IS61LPS102436A-166TQL	100 TQFP, Lead-free
		IS61LPS102436A-166B3	165 PBGA
2Mx18			
	166	IS61LPS204818A-166TQ	100 TQFP
		IS61LPS204818A-166TQL	100 TQFP, Lead-free
		IS61LPS204818A-166B3	165 PBGA

Industrial Range: -40°C to +85°C

Configuration	Frequency	Order Part Number	Package
1Mx36			
	166	IS61LPS102436A-166TQI	100 TQFP
		IS61LPS102436A-166TQLI	100 TQFP, Lead-free
		IS61LPS102436A-166B3I	165 PBGA
		IS61LPS102436A-166B3LI	165 PBGA, Lead-free
2Mx18			
	166	IS61LPS204818A-166TQI	100 TQFP
		IS61LPS204818A-166B3I	165 PBGA



ORDERING INFORMATION (2.5V core/2.5V I/O)

Commercial Range: 0°C to +70°C

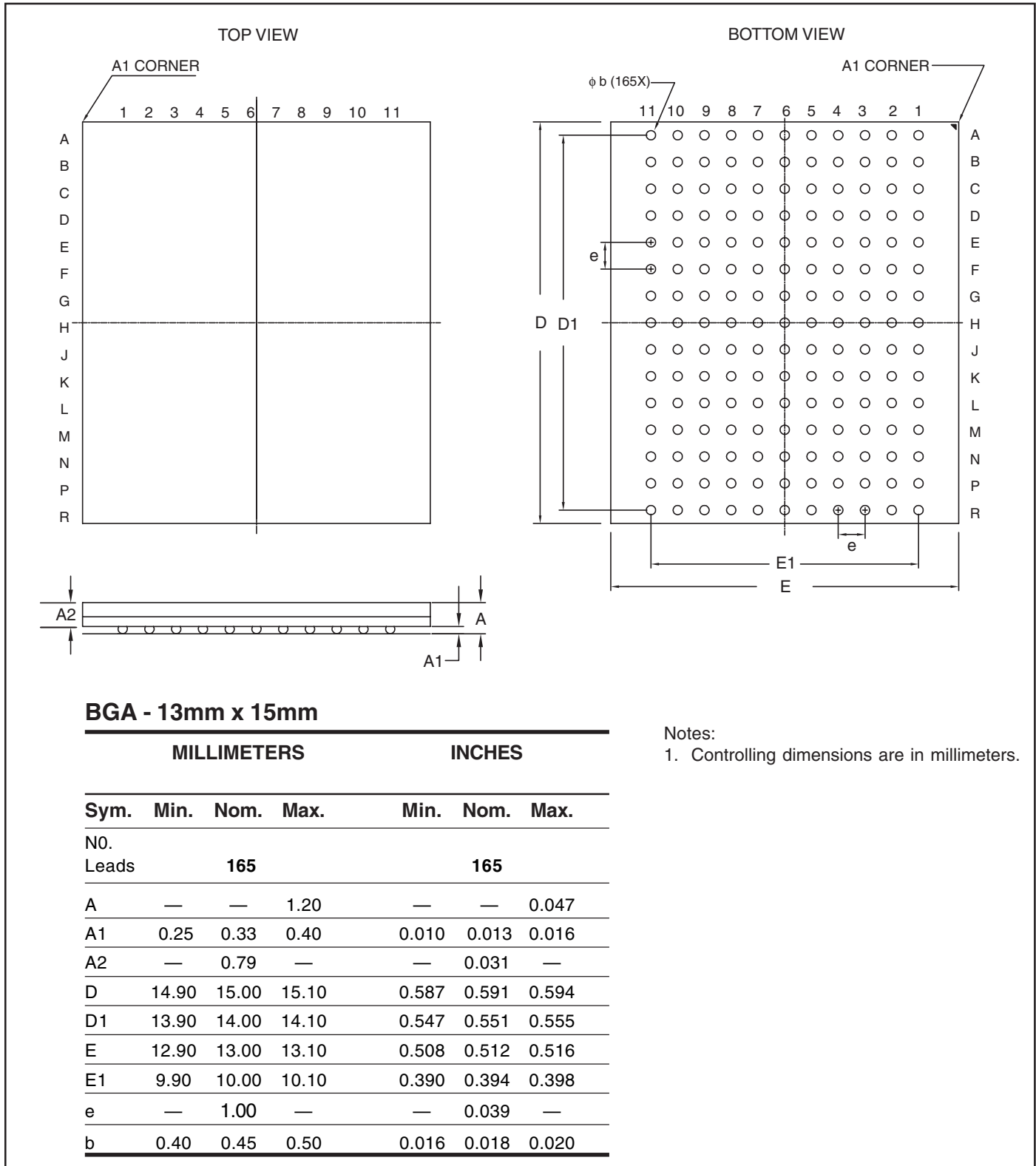
Configuration	Frequency	Order Part Number	Package
1Mx36	166	IS61VPS102436A-166TQ	100 TQFP
		IS61VPS102436A-166TQL	100 TQFP, Lead-free
		IS61VPS102436A-166B3	165 PBGA
2Mx18	166	IS61VPS204818A-166TQ	100 TQFP
		IS61VPS204818A-166TQL	100 TQFP, Lead-free
		IS61VPS204818A-166B3	165 PBGA

Industrial Range: -40°C to +85°C

Configuration	Frequency	Order Part Number	Package
2Mx18	166	IS61VPS204818A-166TQI	100 TQFP
		IS61VPS204818A-166B3I	165 PBGA

PACKAGING INFORMATION

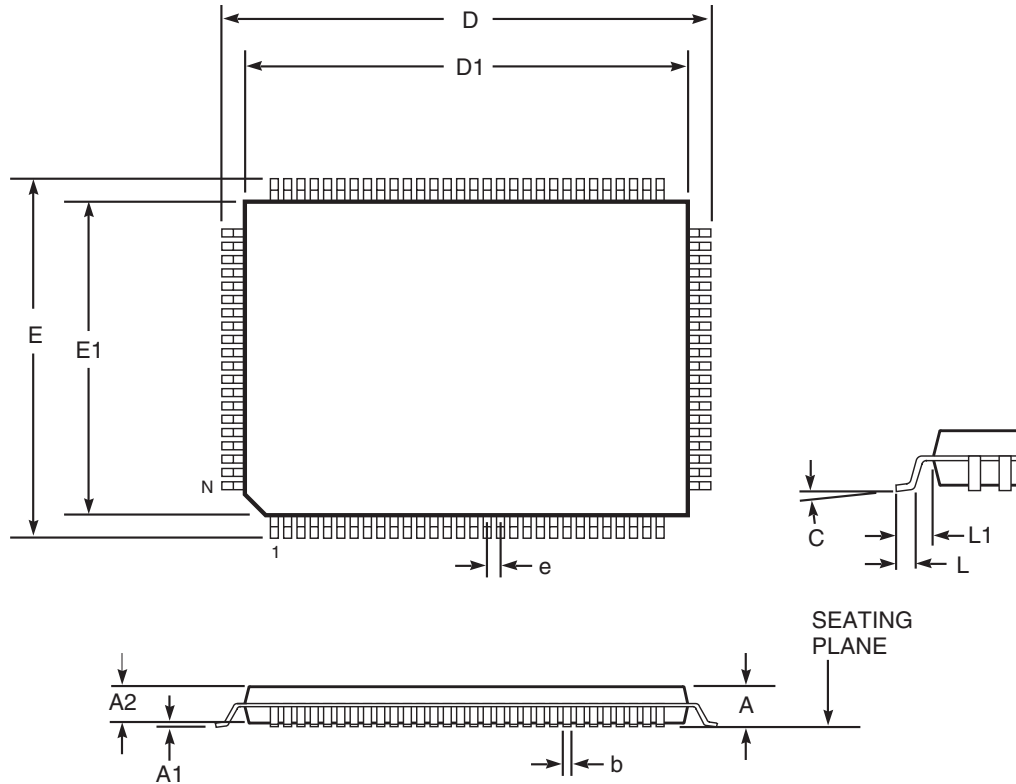
Ball Grid Array Package Code: B (165-pin)



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PACKAGING INFORMATION

TQFP (Thin Quad Flat Pack Package)
Package Code: TQ



Thin Quad Flat Pack (TQ)									
Symbol	Millimeters		Inches		Symbol	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
Ref. Std.									
No. Leads (N)	100				128				
A	—	1.60	—	0.063	—	1.60	—	0.063	
A1	0.05	0.15	0.002	0.006	0.05	0.15	0.002	0.006	
A2	1.35	1.45	0.053	0.057	1.35	1.45	0.053	0.057	
b	0.22	0.38	0.009	0.015	0.17	0.27	0.007	0.011	
D	21.90	22.10	0.862	0.870	21.80	22.20	0.858	0.874	
D1	19.90	20.10	0.783	0.791	19.90	20.10	0.783	0.791	
E	15.90	16.10	0.626	0.634	15.80	16.20	0.622	0.638	
E1	13.90	14.10	0.547	0.555	13.90	14.10	0.547	0.555	
e	0.65 BSC		0.026 BSC		0.50 BSC		0.020 BSC		
L	0.45	0.75	0.018	0.030	0.45	0.75	0.018	0.030	
L1	1.00 REF.		0.039 REF.		1.00 REF.		0.039 REF.		
C	0°	7°	0°	7°	0°	7°	0°	7°	

Notes:

1. All dimensioning and tolerancing conforms to ANSI Y14.5M-1982.
2. Dimensions D1 and E1 do not include mold protrusions. Allowable protrusion is 0.25 mm per side. D1 and E1 do include mold mismatch and are determined at datum plane -H-.
3. Controlling dimension: millimeters.